IN THE CLAIMS:

1. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming an organic insulating film;

forming an opening portion in the organic insulating film;

forming a first conductive film which serves as a barrier ~~so as to be in contact with~~ over the organic insulating film and in the opening portion;

forming a second conductive film including aluminum so as to be in contact with the first conductive film; [[and]]

flattening a surface of the second conductive film by selectively performing a heat treatment under reduced pressure or in normal pressure[[.]]; and

forming a third conductive film in contact with the second conductive film.

2. (Previously Presented) A method for manufacturing a semiconductor device according to claim 1, wherein from the steps of forming the first and the second conductive film to the steps of selectively performing the heat treatment is sequentially carried out without being exposed to atmosphere.

3. (Previously Presented) A method for manufacturing a semiconductor device according to claim 1, wherein irradiation of light from ultraviolet to infrared by a lamp is used as the selective heat treatment.

4. (Currently Amended) A method for manufacturing a semiconductor device according to claim 1, wherein gas laser irradiation or solid-state laser irradiation which performs pulsed oscillation or continuous oscillation is performed as the selective heat treatment for the second conductive film.

5. (Previously Presented) A method for manufacturing a semiconductor device according to claim 1, wherein the organic insulating film includes one kind selected from

acryl, polyimide, polyamide, polyimidamide, epoxyacryl, benzocyclobutene, parylene and flare.

6. (Previously Presented) A method for manufacturing a semiconductor device according to claim 1, wherein the organic insulating film includes a skeleton structure with a bond of silicon (Si) and oxygen (O) and includes at least hydrogen in the substituent, or a film at least including a kind of a fluorine, an alkyl group, and aromatic hydrocarbon in the substituent.

7. (Previously Presented) A method for manufacturing a semiconductor device according to claim 1, wherein a film including titanium, tantalum, tungsten, or silicon is formed as the first conductive film.

8. (Currently Amended) A method for manufacturing a semiconductor device according to claim 1, ~~further comprising the steps of:~~

~~forming a third conductive film over the second conductive film; and~~

wherein the third conductive film includes ~~forming a film including~~ one kind or plural kinds of element selected from germanium, tin, gallium, zinc, lead, indium, or scandium.

9. (Previously Presented) A method for manufacturing a semiconductor device comprising the steps of:

forming an organic insulating film;

forming an opening portion in the organic insulating film;

forming a nitride film so as to be in contact with the organic insulating film and in the opening portion;

patterning the nitride film so that a layer under the organic insulating film is exposed in the opening portion;

forming a first conductive film which serves as a barrier so as to be in contact with the nitride film and the exposed portion of the layer;

forming a second conductive film including aluminum so as to be in contact with the first conductive film; and

flattening a surface of the second conductive film by selectively performing a heat treatment under reduced pressure or in normal pressure.

10. (Previously Presented) A method for manufacturing a semiconductor device according to claim 9, wherein from the steps of forming the first and the second conductive film to the steps of selectively performing the heat treatment is sequentially carried out without being exposed to atmosphere.

11. (Previously Presented) A method for manufacturing a semiconductor device according to claim 9, wherein irradiation of light from ultraviolet to infrared by a lamp is used as the selective heat treatment.

12. (Currently Amended) A method for manufacturing a semiconductor device according to claim 9, wherein gas laser irradiation or solid-state laser irradiation which performs pulsed oscillation or continuous oscillation is performed as the selective heat treatment for the second conductive film.

13. (Previously Presented) A method for manufacturing a semiconductor device according to claim 9, wherein the organic insulating film includes one kind selected from acryl, polyimide, polyamide, polyimidamide, epoxyacryl, benzocyclobutene, parylene and flare.

14. (Previously Presented) A method for manufacturing a semiconductor device according to claim 9, wherein the organic insulating film includes a skeleton structure with a bond of silicon (Si) and oxygen (O) and includes at least hydrogen in the substituent, or a film at least including a kind of a fluorine, an alkyl group, and aromatic hydrocarbon in the substituent.

15. (Previously Presented) A method for manufacturing a semiconductor device according to claim 9, wherein a film including titanium, tantalum, tungsten, or silicon is formed as the first conductive film.

16. (Currently Amended) A method for manufacturing a semiconductor device according to claim 9, further comprising the steps of:

forming a third conductive film over the second conductive film; ~~and~~

~~forming a film including~~ wherein the third conductive film includes one kind or plural kinds of element selected from germanium, tin, gallium, zinc, lead, indium, or scandium.

17. (Previously Presented) A method for manufacturing a semiconductor device comprising the steps of:

forming an organic insulating film;

forming an opening portion in the organic insulating film;

forming a first conductive film on the organic insulating film and in the opening portion;

forming a second conductive film including aluminum on the first conductive film and in the opening portion; and

flattening a surface of the second conductive film by performing a heat treatment under reduced pressure or in normal pressure.

18. (Previously Presented) A method for manufacturing a semiconductor device according to claim 17, wherein from the steps of forming the first and the second conductive film to the steps of performing the heat treatment is sequentially carried out without being exposed to atmosphere.

19. (Previously Presented) A method for manufacturing a semiconductor device according to claim 17, wherein irradiation of light from ultraviolet to infrared by a lamp is used as the heat treatment.

20. (Currently Amended) A method for manufacturing a semiconductor device according to claim 17, wherein gas laser irradiation or solid-state laser irradiation which performs pulsed oscillation or continuous oscillation is performed as the heat treatment for the second conductive film.

21. (Previously Presented) A method for manufacturing a semiconductor device according to claim 17, wherein the organic insulating film includes one kind selected from acryl, polyimide, polyamide, polyimidamide, epoxyacryl, benzocyclobutene, parylene and flare.

22. (Previously Presented) A method for manufacturing a semiconductor device according to claim 17, wherein the organic insulating film includes a skeleton structure with a bond of silicon (Si) and oxygen (O) and includes at least hydrogen in the substituent, or a film at least including a kind of a fluorine, an alkyl group, and aromatic hydrocarbon in the substituent.

23. (Previously Presented) A method for manufacturing a semiconductor device according to claim 17, wherein a film including titanium, tantalum, tungsten, or silicon is formed as the first conductive film.

24. (Currently Amended) A method for manufacturing a semiconductor device according to claim 17, further comprising the steps of:

forming a third conductive film over the second conductive film; ~~and~~

~~forming a film including~~ wherein the third conductive film includes one kind or plural kinds of element selected from germanium, tin, gallium, zinc, lead, indium, or scandium.

25. (Previously Presented) A method for manufacturing a semiconductor device comprising the steps of:

forming an organic insulating film;

forming an opening portion in the organic insulating film;

forming a nitride film on the organic insulating film and in the opening portion;

patterning the nitride film so that a layer under the organic insulating film is exposed in the opening portion;

forming a first conductive film on the nitride film and the exposed portion of the layer;

forming a second conductive film including aluminum on the first conductive film and in the opening portion; and

flattening a surface of the second conductive film by performing a heat treatment under reduced pressure or in normal pressure.

26. (Previously Presented) A method for manufacturing a semiconductor device according to claim 25, wherein from the steps of forming the first and the second conductive film to the steps of performing the heat treatment is sequentially carried out without being exposed to atmosphere.

27. (Previously Presented) A method for manufacturing a semiconductor device according to claim 25, wherein irradiation of light from ultraviolet to infrared by a lamp is used as the heat treatment.

28. (Currently Amended) A method for manufacturing a semiconductor device according to claim 25, wherein gas laser irradiation or solid-state laser irradiation which performs pulsed oscillation or continuous oscillation is performed as the heat treatment for the second conductive film.

29. (Previously Presented) A method for manufacturing a semiconductor device according to claim 25, wherein the organic insulating film includes one kind selected from acryl, polyimide, polyamide, polyimidamide, epoxyacryl, benzocyclobutene, parylene and flare.

30. (Previously Presented) A method for manufacturing a semiconductor device according to claim 25, wherein the organic insulating film includes a skeleton structure with a bond of silicon (Si) and oxygen (O) and includes at least hydrogen in the substituent, or a film at least including a kind of a fluorine, an alkyl group, and aromatic hydrocarbon in the substituent.

31. (Previously Presented) A method for manufacturing a semiconductor device according to claim 25, wherein a film including titanium, tantalum, tungsten, or silicon is formed as the first conductive film.

32. (Currently Amended) A method for manufacturing a semiconductor device according to claim 25, further comprising the steps of:

forming a third conductive film over the second conductive film; ~~and~~

~~forming a film including~~ wherein the third conductive film includes one kind or plural kinds of element selected from germanium, tin, gallium, zinc, lead, indium, or scandium.

33. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming an organic insulating film;

forming an opening portion in the organic insulating film;

forming a first conductive film so as to be in contact with the organic insulating film and in the opening portion;

forming a second conductive film including aluminum so as to be in contact with the first conductive film; and

flattening a surface of the second conductive film by selectively performing a laser irradiation which performs pulsed oscillation or continuous oscillation under reduced pressure or in normal pressure for the second conductive film.

34. (Previously Presented) A method for manufacturing a semiconductor device according to claim 33, wherein from the steps of forming the first and the second conductive film to the steps of selectively performing the laser irradiation is sequentially carried out without being exposed to atmosphere.

35. (Previously Presented) A method for manufacturing a semiconductor device according to claim 33, wherein the organic insulating film includes one kind selected from acryl, polyimide, polyamide, polyimidamide, epoxyacryl, benzocyclobutene, parylene and flare.

36. (Previously Presented) A method for manufacturing a semiconductor device according to claim 33, wherein the organic insulating film includes a skeleton structure with a bond of silicon (Si) and oxygen (O) and includes at least hydrogen in the substituent, or a film at least including a kind of a fluorine, an alkyl group, and aromatic hydrocarbon in the substituent.

37. (Previously Presented) A method for manufacturing a semiconductor device according to claim 33, wherein a film including titanium, tantalum, tungsten, or silicon is formed as the first conductive film.

38. (Currently Amended) A method for manufacturing a semiconductor device according to claim 33, further comprising the steps of:

forming a third conductive film over the second conductive film; ~~and~~

~~forming a film including~~ wherein the third conductive film includes one kind or plural kinds of element selected from germanium, tin, gallium, zinc, lead, indium, or scandium.

39. (Currently Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming an organic insulating film;

forming an opening portion in the organic insulating film;

forming a nitride film so as to be in contact with the organic insulating film and in the opening portion;

patterning the nitride film so that a layer under the organic insulating film is exposed in the opening portion;

forming a first conductive film so as to be in contact with the nitride film and the exposed portion of the layer;

forming a second conductive film including aluminum so as to be in contact with the first conductive film; and

flattening a surface of the second conductive film by selectively performing a laser irradiation which performs pulsed oscillation or continuous oscillation under reduced pressure or in normal pressure for the second conductive film.

40. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein from the steps of forming the first and the second conductive film to the steps of selectively performing the laser irradiation is sequentially carried out without being exposed to atmosphere.

41. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the organic insulating film includes one kind selected from acryl, polyimide, polyamide, polyimidamide, epoxyacryl, benzocyclobutene, parylene and flare.

42. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein the organic insulating film includes a skeleton structure with a bond of silicon (Si) and oxygen (O) and includes at least hydrogen in the substituent, or a film at least including a kind of a fluorine, an alkyl group, and aromatic hydrocarbon in the substituent.

43. (Previously Presented) A method for manufacturing a semiconductor device according to claim 39, wherein a film including titanium, tantalum, tungsten, or silicon is formed as the first conductive film.

44. (Currently Amended) A method for manufacturing a semiconductor device according to claim 39, further comprising the steps of:

forming a third conductive film over the second conductive film; ~~and~~

~~forming a film including~~ wherein the third conductive film includes one kind or plural kinds of element selected from germanium, tin, gallium, zinc, lead, indium, or scandium.